

Avionics Pulsed Power Transistor 350 W, 960 - 1215 MHz, 10 µs Pulse, 10 % Duty

Rev. V1

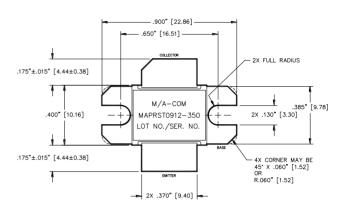
Features

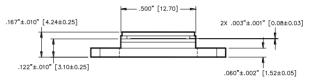
- NPN silicon microwave power transistors
- · Common base configuration
- Broadband Class C operation
- · High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS* Compliant

Absolute Maximum Ratings @ +25°C

Parameter	Symbol	Rating
Collector-Emitter Voltage	V _{CES}	65 V
Emitter-Base Voltage	V_{EBO}	3 V
Collector Current (Peak)	Ic	32.5 A
Power Dissipation	P _{TOT}	1.34 kW
Storage Temperature	T _{STG}	-65°C to +200°C
Junction Temperature	TJ	+200°C

Outline Drawing





UNLESS OTHERWISE NOTED, TOLERANCES ARE INCHES ±.005" [MILLIMETERS ±0.13mm]

Electrical Specifications: $V_{CC} = 50 \text{ V}$, $P_{IN} = 40 \text{ W}$, $T_A = 25 \pm 5^{\circ}\text{C}$ (unless otherwise noted)

Parameter	Symbol	Test Conditions	Units	Min.	Max.
Collector-Emitter Breakdown Voltage	BV _{CES}	$I_C = 50 \text{ mA}$	V	65	-
Collector-Emitter Leakage Current	I _{CES}	V _{CE} = 50 V	mA	-	15
Thermal Resistance	R _{TH(JC)}	F = 960, 1090, 1215 MHz	°C/W	-	0.13
Output Power	Po	F = 960, 1090, 1215 MHz	W	350	-
Power Gain	G _P	F = 960, 1090, 1215 MHz	dB	9.4	-
Collector Efficiency	h _C	F = 960, 1090, 1215 MHz	%	45	-
Input Return Loss	RL	F = 960, 1090, 1215 MHz	dB	-	-9
Load Mismatch Stability	VSWR-T	F = 960 MHz	-	-	10:1
Load Mismatch Tolerance	VSWR-S	F = 960, 1090, 1215 MHz	-	-	1.5:1

^{*} Restrictions on Hazardous Substances, European Union Directive 2011/65/EU.

MAPRST0912-350



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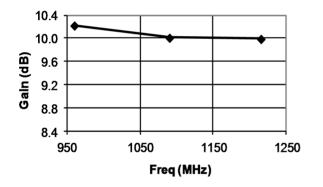
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Typical RF Performance

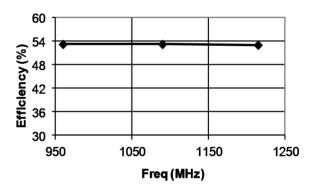
Freq.	P _{IN}	P _{OUT}	Gain	∆Gain	Ic	Eff	RL		VSWR-T	P1dB Overdrive	
(MHz)	(W)	(W)	(dB)	(dB)	(A)	(%)	(dB)		(10:1)	P _{OUT} (W)	Δ P _O (dB)
960	40	421	10.22	_	15.7	53.4	-19.9	S	Р	496	0.72
1090	40	401	10.01	_	15.0	53.4	-18.5	S	_	469	0.69
1215	40	399	9.99	0.23	15.0	53.2	-21.5	S	_	421	0.22

Note: $\triangle Po(dB)$ is the difference between P_{OUT} at 1dB overdrive and P_{OUT} at P_{IN} = 40W.

Gain vs. Frequency



Collector Efficiency vs. Frequency

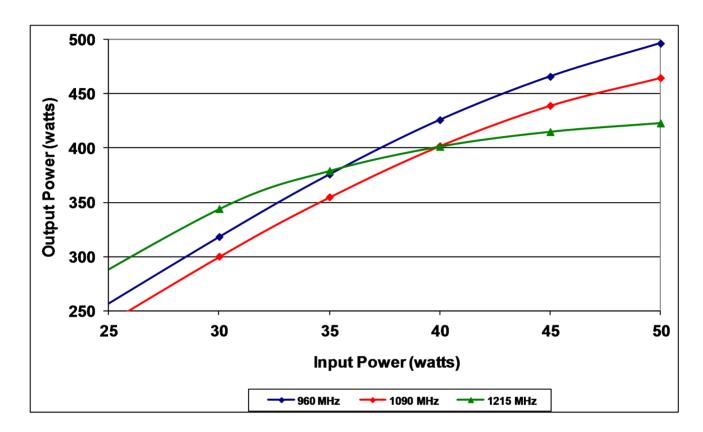




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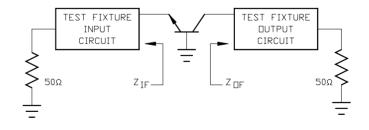
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RF Power Transfer Curve (Output Power Vs. Input Power)



Broadband Test Fixture Impedance

F (MHz)	Z _{IF} (Ω)	Z _{OF} (Ω)
960	1.8 - j1.7	1.7 - j1.7
1030	1.7 - j1.4	1.8 - j1.2
1090	1.6 - j1.2	1.9 - j0.8
1150	1.4 - j1.0	1.9 - j0.6
1215	1.2 - j0.8	2.0 - j0.2

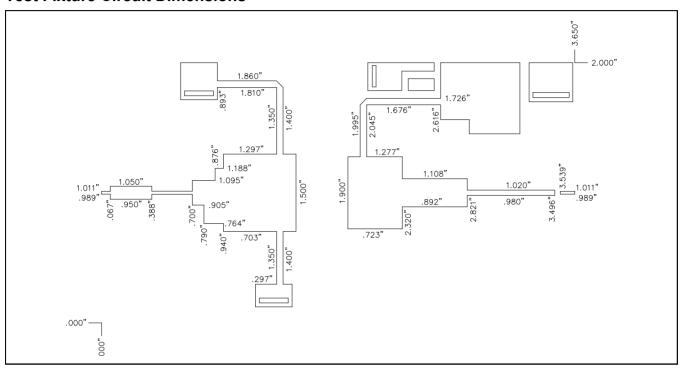




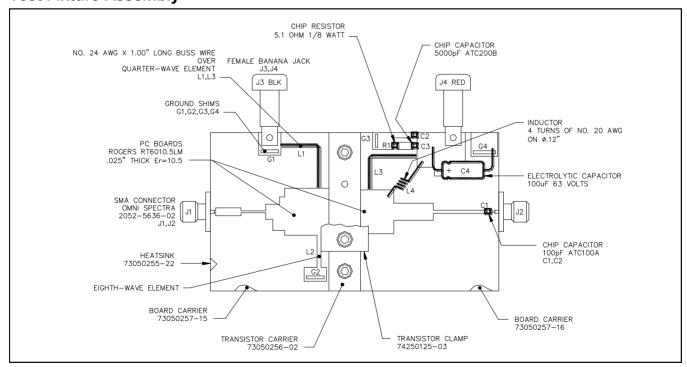
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Test Fixture Circuit Dimensions



Test Fixture Assembly



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